



Reg. No. : .....

Name : .....



K20U 0319

**II Semester B.Sc. Degree (CBCSS – Supplementary/Improvement)  
Examination, April 2020  
CORE COURSE IN PHYSICS  
2B02 PHY : Electronics – I  
(2014-2018 Admissions)**

Time : 3 Hours

Max. Marks : 40

**SECTION – A**

All questions are to be answered – Very short answer type – **Each** question carries 1 mark.

1. The base of a transistor is \_\_\_\_\_ doped.
2. A JFET is a \_\_\_\_\_ driven device.
3. Convert  $4285_8$  into binary.
4. With a NAND latch a low R and a low S produce a \_\_\_\_\_ condition.

**SECTION – B**

7 questions are to be answered. Short answer questions – **Each** question carries 2 marks.

5. What is faithful amplification ? What are the basic conditions in order to obtain the same ?
6. State De Morgan's theorem.
7. What do you mean by overflow and underflow ?
8. What is the need of biasing a transistor ?
9. What is the difference between JFET and bipolar transistor ?
10. Why NAND gate is called a universal gate ?

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11. What is pinch off voltage in JFET ?
12. Explain AND gate with 2 input terminals.
13. What is the decimal number for 1111.01 ?
14. What do you mean by operating point ?

## SECTION – C

**Four** questions are to be answered – Short essay/problem type – **Each** question carries **3** marks.

15. What is meant by dc load line of a transistor circuit ? Explain saturation region, cutoff region and active region of a transistor characteristics.
16. Explain the function of XOR gate with the help of a diagram. Draw the truth table for a 3-input XOR gate.
17. What is meant by odd parity and even parity ?
18. The device parameters for n-channel JFET are :  
Maximum current  $I_{DSS} = 10 \text{ mA}$ , pinch off voltage  $V_p = -4 \text{ V}$ . Calculate the drain current for  $V_{GS} = 0, -10 \text{ V}, -4 \text{ V}$ .
19. In a transistor circuit, collector load is  $4 \text{ k}\Omega$  where as the zero signal collector current is  $1 \text{ mA}$ . Calculate (a) the operating point if  $V_{CC} = 10 \text{ V}$  (b) What will be the operating point if  $R_{CC} = 5 \text{ k}\Omega$ .
20. The collector leakage current in a transistor is  $250 \mu\text{A}$  in CE arrangement. If the transistor is connected in CB arrangement, what will be the leakage current ? Given  $\beta = 100$ .

## SECTION – D

**Two** questions are to be answered – Long essay type – **Each** question carries **5** marks.

21. Explain the working and characteristics of CE amplifier.
22. Explain construction and working of a JFET.
23. Describe positional number system. What is the general form of a positional number system ? Explain binary, decimal and hexadecimal number system.
24. Explain the working of half adder and full adder using logic gates.